

ABSTRACT

A phase-change memory cell including, between two electrical contacts, a portion in a memory material with amorphous-crystalline phase-change and vice versa, as a stack with a central area located between two outmost areas. An interface, inert or quasi-inert from a physico-chemical point of view, is present between the active central area and each passive outmost area. Each passive outmost area is made in a material having a melting temperature higher than that of the material of the active central area.